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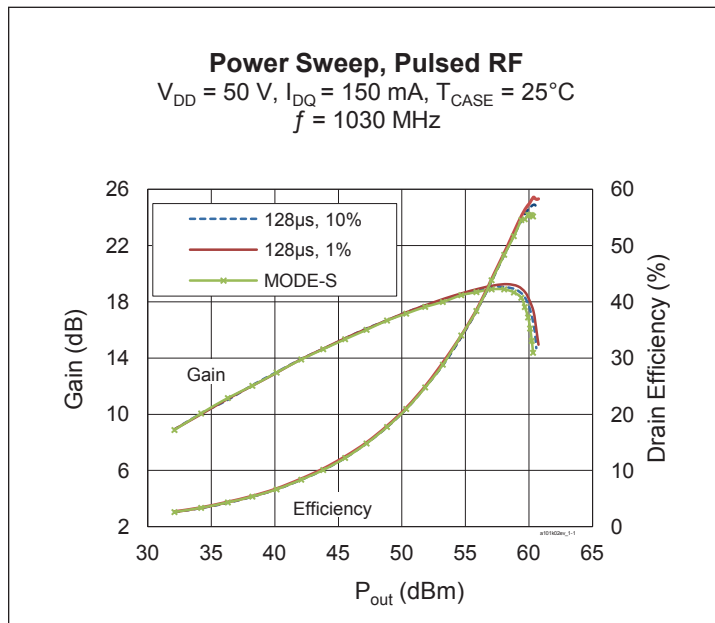
Thermally-Enhanced High Power RF LDMOS FET 1000 W, 50 V, 1030 / 1090 MHz

Description

The PTVA101K02EV LDMOS FET is designed for use in power amplifier applications in the 1030 MHz / 1090 MHz frequency band. Features include high gain and thermally-enhanced package with bolt-down flange. Manufactured with Infineon's advanced LDMOS process, this device provides excellent thermal performance and superior reliability.



PTVA101K02EV
Package H-36275-4



Features

- Broadband input matching
- High gain and efficiency
- Integrated ESD protection
- Low thermal resistance
- Pb-free and RoHS compliant
- Capable of withstanding a 10:1 load mismatch (all phase angles) at 1000 W under MODE-S pulse condition, (32µS ON / 18µS OFF) X 80, LTDF = 6.4%.

RF Characteristics

Pulsed RF Performance (tested in Infineon test fixture)

$V_{DD} = 50\text{ V}$, $I_{DQ} = 0.15\text{ A}$, $P_{OUT} = 900\text{ W}$, $f = 1030\text{ MHz}$, 128 µs pulse width, 10% duty cycle

Characteristic	Symbol	Min	Typ	Max	Unit
Gain	G_{ps}	17	18	21	dB
Drain Efficiency	η_D	62	65	—	%

All published data at $T_{CASE} = 25^\circ\text{C}$ unless otherwise indicated

ESD: Electrostatic discharge sensitive device—observe handling precautions!

RF Characteristics

Typical RF Performance (not subject to production test, verified by design/characterization in Infineon test fixture)

$V_{DD} = 50\text{ V}$, $I_{DQ} = 75\text{ mA}$ per side, Input signal ($t_r = 5\text{ ns}$, $t_f = 6.5\text{ ns}$), $T_{CASE} = 25^\circ\text{C}$, class AB test

Mode of operation	f (MHz)	IRL (dB)	P_{1dB}			P_{3dB}			$P_{\text{droop(pulse)}}$ dB @ 1000 W	t_r (ns)	t_f (ns)
			Gain (dB)	Eff (%)	P_{OUT} (W)	Gain (dB)	Eff (%)	P_{OUT} (W)			
128 μs , 10%	1030	20	18	56	980	16	57	1090	0.18	7	8
128 μs , 1%	1030	20	18.1	57	1010	16.1	58	1130	0.16	7	8
MODE-S (32 μs ON / 18 μs OFF)X80, LTDF=6.4%	1030	20	17.9	54	930	14.9	55	1060	0.45	7	8
128 μs , 10%	1090	13	18.3	59	920	16.2	60	1050	0.16	7	8
128 μs , 1%	1090	14	18.4	60	950	16.4	61	1080	0.17	7	8

DC Characteristics (each side)

Characteristic	Conditions	Symbol	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	$V_{GS} = 0\text{ V}$, $I_{DS} = 10\text{ mA}$	$V_{(BR)DSS}$	105	—	—	V
Drain Leakage Current	$V_{DS} = 50\text{ V}$, $V_{GS} = 0\text{ V}$	I_{DSS}	—	—	1	μA
	$V_{DS} = 105\text{ V}$, $V_{GS} = 0\text{ V}$	I_{DSS}	—	—	10	μA
On-State Resistance	$V_{GS} = 10\text{ V}$, $V_{DS} = 0.1\text{ V}$	$R_{DS(on)}$	—	0.1	—	Ω
Operating Gate Voltage	$V_{DS} = 50\text{ V}$, $I_{DQ} = 150\text{ mA}$	V_{GS}	3	3.35	4	V
Gate Leakage Current	$V_{GS} = 10\text{ V}$, $V_{DS} = 0\text{ V}$	I_{GSS}	—	—	1.0	μA

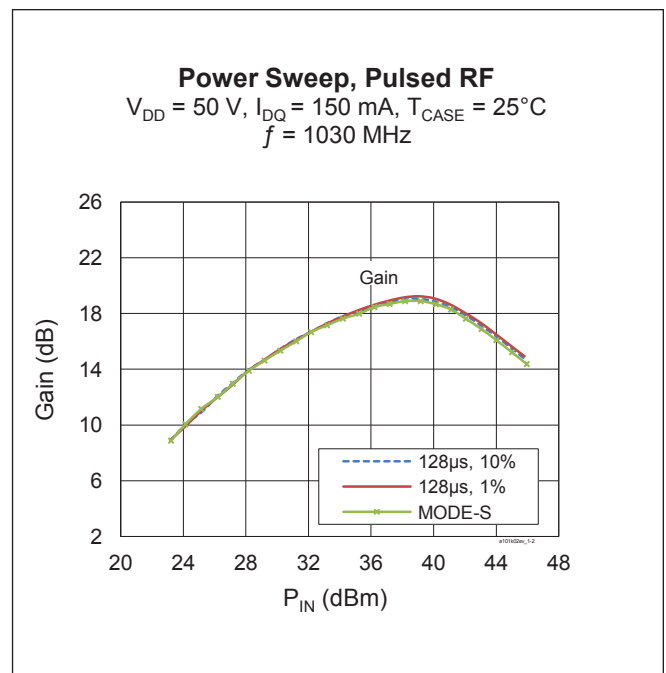
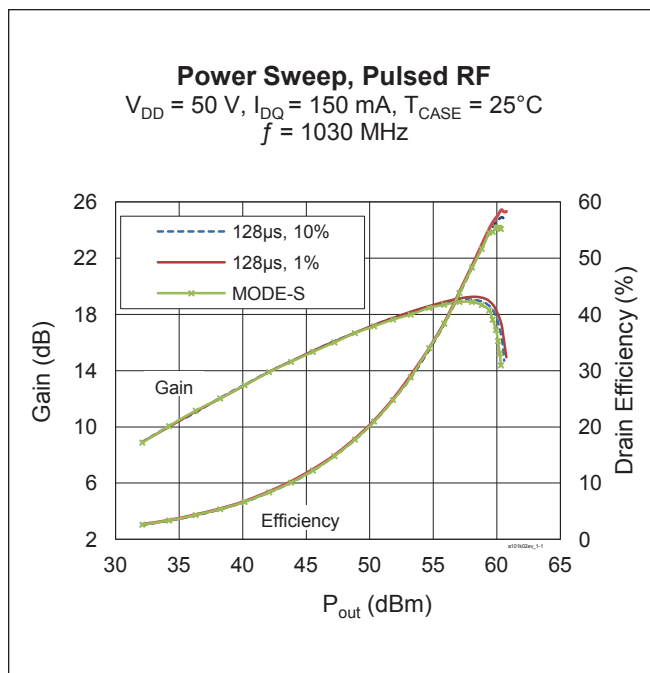
Maximum Ratings

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DSS}	105	V
Gate-Source Voltage	V_{GS}	-6 to +12	V
Junction Temperature	T_J	200	$^\circ\text{C}$
Storage Temperature Range	T_{STG}	-65 to +150	$^\circ\text{C}$
Thermal Resistance ($T_{CASE} = 70^\circ\text{C}$, 1000 W, MODE-S)	$R_{\theta JC}$	0.16	$^\circ\text{C/W}$

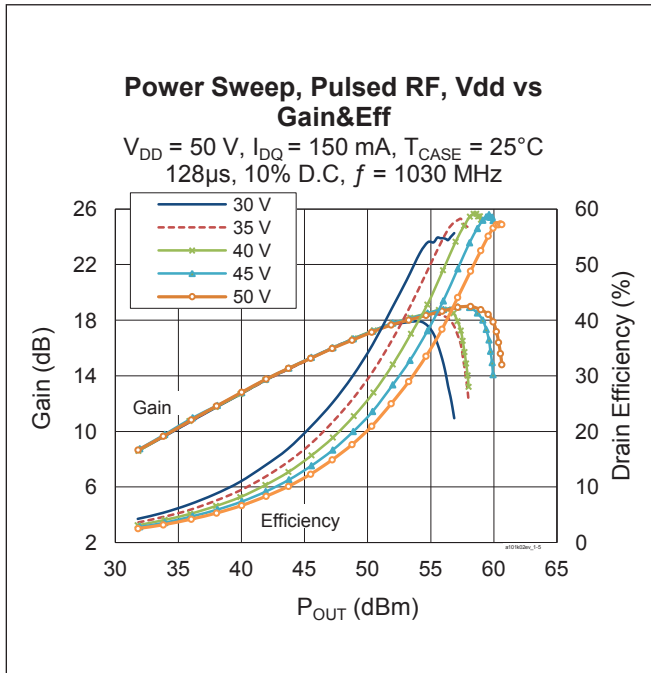
Ordering Information

Type and Version	Order Code	Package and Description	Shipping
PTVA101K02EV V1	PTVA101K02EVV1XWSA1	H-36275-4, bolt-down	Tray
PTVA101K02EV V1 R250	PTVA101K02EVV1R250XTMA1	H-36275-4, bolt-down	Tape & Reel, 250pcs

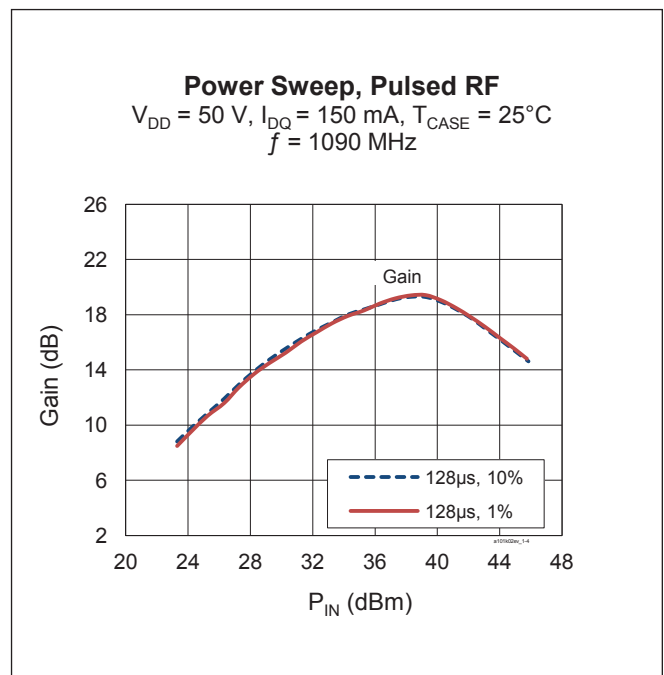
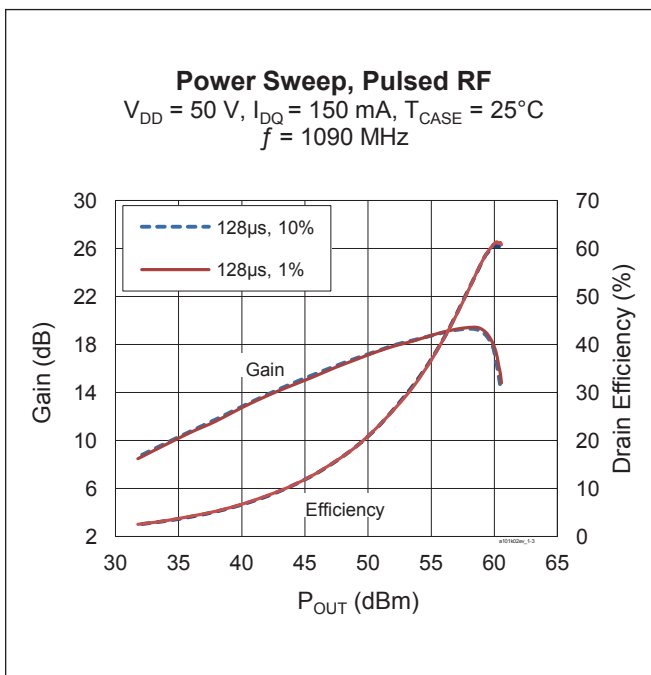
Typical RF Performance (tested with LTN/PTVA101K02EV V1 test fixture, 1030 MHz)



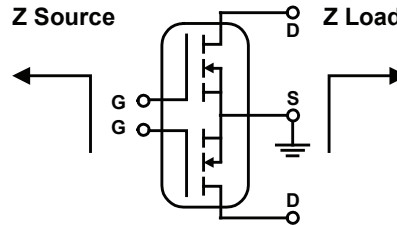
Typical RF Performance (cont.) (tested with LTN/PTVA101K02EV V1 test fixture, 1030 MHz)



Typical RF Performance (tested with LTN/PTVA101K02EV E6 test fixture, 1090 MHz)



Broadband Circuit Impedance



Freq [MHz]	Z Source Ω		Z Load Ω	
	R	jX	R	jX
1030	2.00	1.51	1.48	0.07
1090	2.35	0.64	1.12	-0.28

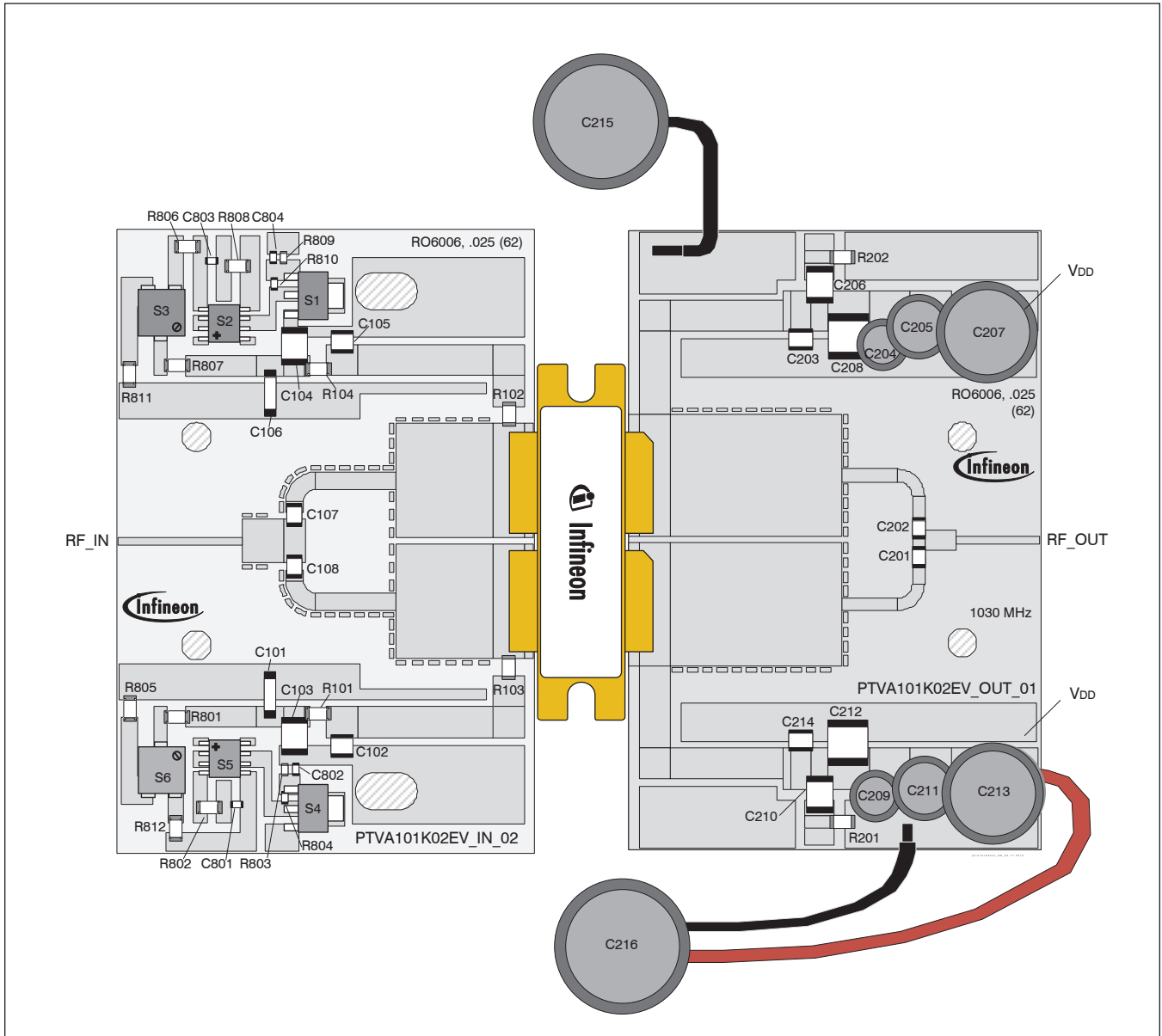
Note: Measurement on single side.

Load Pull Performance

Each Side Load Pull Performance –16 μ s pulse width, 10% duty cycle, class AB, $V_{DD} = 50$ V, 100 mA

Freq [MHz]	Max Output Power					Max Efficiency					Z Optimum					
	P _{OUT} [dBm]	P _{OUT} [W]	Eff [%]	Gain [dB]	Z _{Load} [Ω]	P _{OUT} [dBm]	P _{OUT} [W]	Eff [%]	Gain [dB]	Z _{Load} [Ω]	P _{OUT} [dBm]	P _{OUT} [W]	Eff [%]	Gain [dB]	Z _{Load} [Ω]	Z _{Source} [Ω]
960	58.10	645.65	61.90	16.46	1.14 – j0.08	56.00	398.11	72.20	18.68	0.79 + j0.69	57.50	562.34	68.00	17.50	0.91 + j0.33	1.41 – j1.62
1030	57.80	602.56	55.60	16.00	0.91 – j0.08	56.00	398.11	71.00	18.80	0.71 + j0.66	57.10	512.86	65.00	17.50	0.78 + j0.34	1.76 – j2.12
1090	57.90	616.60	61.80	16.95	0.95 + j0.27	56.20	416.87	69.80	18.68	0.83 + j0.90	57.40	549.54	65.70	17.73	0.87 + j0.62	2.34 – j2.39
1150	57.36	544.50	50.52	15.80	1.11 + j0.12	56.90	489.78	65.00	17.63	0.94 + j0.76	57.20	524.81	61.20	17.00	1.01 + j0.48	3.21 – j1.47
1215	57.26	532.11	53.90	15.60	1.20 + j0.01	55.40	346.74	62.30	17.46	0.59 + j0.81	56.70	467.74	58.45	16.60	0.88 + j0.49	2.37 – j0.84

Reference Circuit (LTN/PTVA101K02EV V1 test fixture, 1030 MHz)



Reference circuit assembly diagram (not to scale)*

Reference Circuit (cont.)

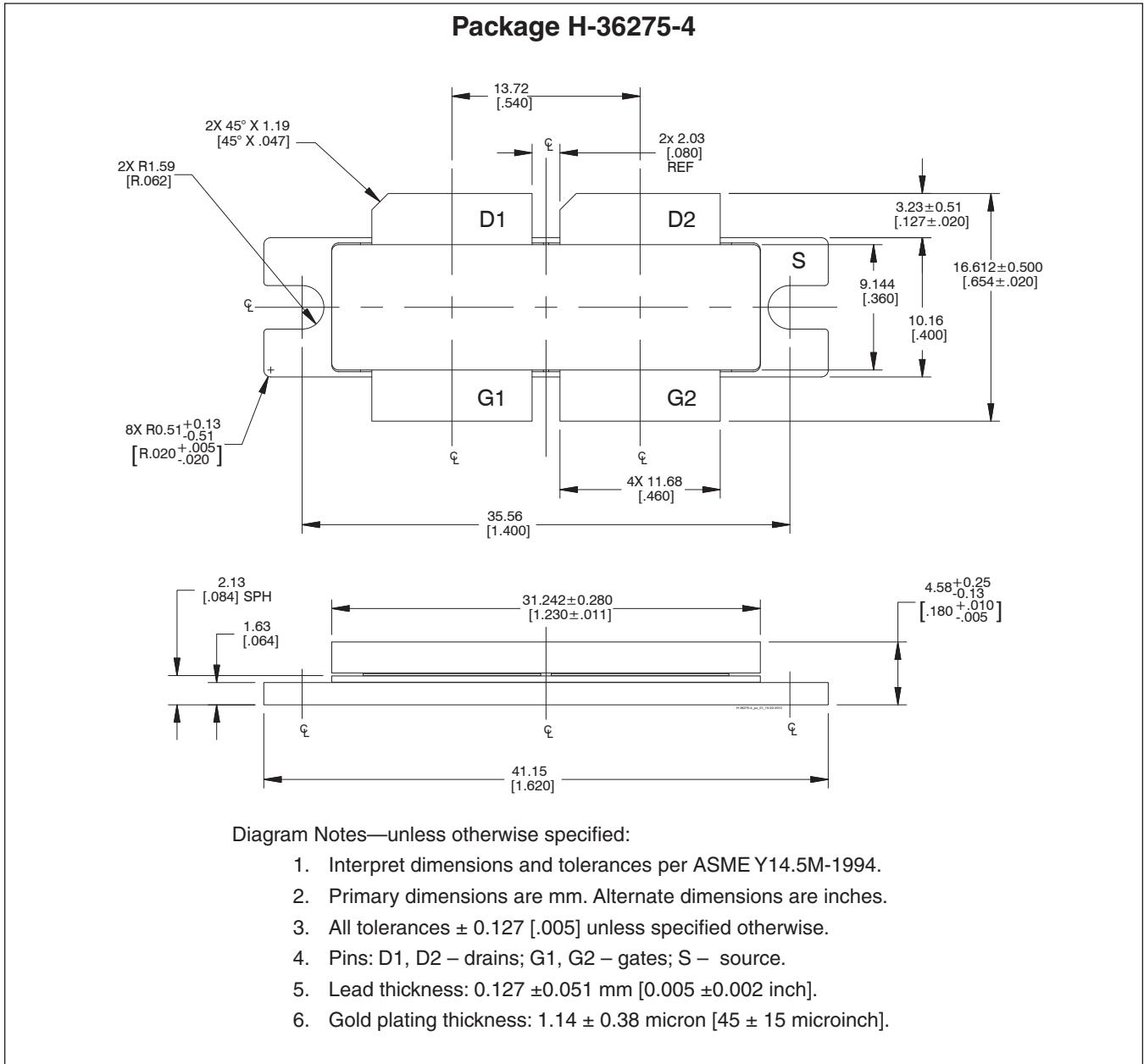
Reference Circuit Assembly

DUT	Test Fixture Part No.	PCB	Frequency (MHz)
PTVA101K02EV	LTN/PTVA101K02EV V1	Rogers 6006, 0.635 mm [0.025"] thick, 2 oz. copper, $\epsilon_r = 6.15$	1030 MHz
PTVA101K02EV	LTN/PTVA101K02EV E4	Rogers 6006, 0.635 mm [0.025"] thick, 2 oz. copper, $\epsilon_r = 6.15$	1090 MHz
PTVA101K02EV	LTN/PTVA101K02EV E6	Rogers 3010, 0.635 mm [0.025"] thick, 2 oz. copper, $\epsilon_r = 10.2$	1090 MHz
PTVA101K02EV	LTN/PTVA101K02EV E8	Rogers 3010, 0.635 mm [0.025"] thick, 2 oz. copper, $\epsilon_r = 10.2$	1030 MHz

Components Information

Component	Description	Suggested Manufacturer	P/N
Input			
C101, C106	Capacitor, 10 μ F	TDK Corporation	C5750X5R1H106K230KA
C102, C105, C107, C108	Capacitor, 39 pF	ATC	ATC100B390KW500XB
C103, C104	Capacitor, 1 μ F	TDK Corporation	C4532X7R2A105M230KA
C801, C802, C803, C804	Capacitor, 1000 pF	Panasonic Electronic Components	ECJ-1VB1H102K
R101, R104, R801, R807	Resistor, 10 Ohm	Panasonic Electronic Components	ERJ-8GEYJ100V
R102, R103	Resistor, 100 Ohm	Panasonic Electronic Components	ERJ-8GEYJ101V
R802, R808	Resistor, 6200 Ohm	Panasonic Electronic Components	ERJ-8GEYJ623V
R803, R809	Resistor, 1300 Ohm	Panasonic Electronic Components	ERJ-3GEYJ132V
R804, R810	Resistor, 1200 Ohm	Panasonic Electronic Components	ERJ-3GEYJ122V
R805, R806, R811, R812	Resistor, 2000 Ohm	Panasonic Electronic Components	ERJ-8GEYJ202V
S1, S4	Transistor	Infineon Technologies	BCP56
S2, S5	Voltage regulator	National Semiconductor	LM7805
S3, S6	Potentiometer, 2k ohm	Bourns Inc.	3224W-202ECT-ND
Output			
C201, C202, C203, C214	Capacitor, 39 pF	ATC	ATC100B390KW500XB
C204, C209	Capacitor, 100 μ F	Panasonic Electronic Components	EEV-HD1V101P
C205, C211	Capacitor, 22 μ F	Cornell Dubilier Electronics (CDE)	SEK220M100ST
C206, C210	Capacitor, 1 μ F	TDK Corporation	C4532X7R2A105M230KA
C207, C213	Capacitor, 100 μ F	Cornell Dubilier Electronics (CDE)	SK101M100ST
C208, C212	Capacitor, 10 μ F	TDK Corporation	C5750X5R1H106K230KA
C215, C216	Capacitor, 6800 μ F	Panasonic Electronic Components	ECO-S2AP682EA
R201, R202	Resistor, 5600 Ohm	Panasonic Electronic Components	ERJ-8GEYJ562V

Package Outline Specifications



Find the latest and most complete information about products and packaging at the Infineon Internet page <http://www.infineon.com/rfpower>

Revision History: 2013-04-15 Data Sheet

Previous Version: 2012-06-07, Preliminary Data Sheet

Page	Subjects (major changes since last revision)
All	Data Sheet reflects released product specifications

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Edition 2013-04-15

**Published by
Infineon Technologies AG
81726 Munich, Germany**

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